

TO-92 Plastic-Encapsulate Transistors

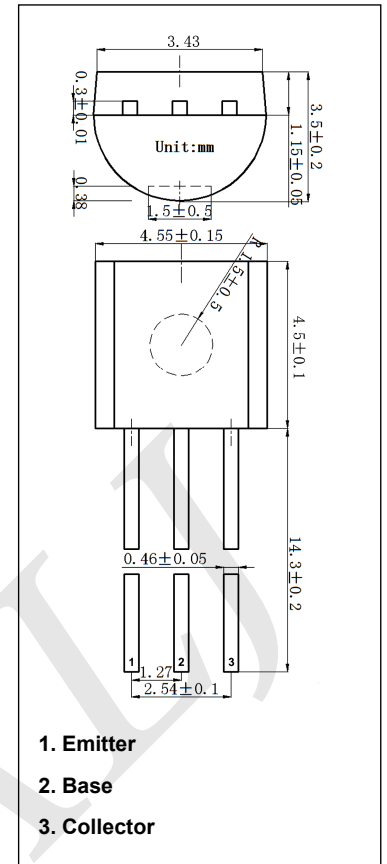
S8550D331 PNP Transistors

Features

- Excellent h_{FE} Linearity

Maximum Ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector Base Voltage	-40	V
V_{CEO}	Collector Emitter Voltage	-25	V
V_{EBO}	Emitter Base Voltage	-5	V
I_C	Collector Current	-800	mA
P_C	Collector Power Dissipation	625	mW
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	- 55 to +150	$^\circ\text{C}$



Electrical Characteristics ($T_a=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=-100\mu\text{A}, I_E=0$	-40			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-1\text{mA}, I_B=0$	-25			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-100\mu\text{A}, I_C=0$	-5			V
I_{CBO}	Collector cut-off current	$V_{CB}=-40\text{V}, I_E=0$			-100	nA
I_{CEO}	Collector cut-off current	$V_{CE}=-20\text{V}, I_B=0$			-100	nA
I_{EBO}	Emitter cut-off current	$V_{EB}=-3\text{V}, I_C=0$			-100	nA
$h_{FE(1)}$	DC current gain	$V_{CE}=-1\text{V}, I_C=-50\text{mA}$	100		200	
$h_{FE(2)}$		$V_{CE}=-1\text{V}, I_C=-500\text{mA}$	50			
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C=-500\text{mA}, I_B=-50\text{mA}$			-0.6	V
$V_{BE(sat)}$	Base-emitter saturation voltage	$I_C=-500\text{mA}, I_B=-50\text{mA}$			-1.2	V
f_T	Transition frequency	$V_{CE}=-6\text{V}, I_C=-20\text{mA}, f=30\text{MHz}$	150			MHz

Typical Characteristics

